

Qingjiang Li

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	<i>In Situ</i> Learning in Hardware Compatible Multilayer Memristive Spiking Neural Network. IEEE Transactions on Cognitive and Developmental Systems, 2022, 14, 448-461.	3.8	6
2	A Configurable Artificial Neuron Based on a Threshold-Tunable TiN/NbO ₂ /Pt Memristor. IEEE Electron Device Letters, 2022, 43, 631-634.	3.9	17
3	Network Pruning Towards Highly Efficient RRAM Accelerator. IEEE Nanotechnology Magazine, 2022, 21, 340-351.	2.0	0
4	Binary Memristive Synapse Based Vector Neural Network Architecture and Its Application. IEEE Transactions on Circuits and Systems II: Express Briefs, 2021, 68, 772-776.	3.0	2
5	A bidirectional threshold switching selector with a symmetric multilayer structure. Science China Information Sciences, 2021, 64, 1.	4.3	4
6	Calibration strategy of the JUNO experiment. Journal of High Energy Physics, 2021, 2021, 1.	4.7	39
7	EEG Signal Epilepsy Detection System Based on Convolutional Neural Network and Memristor Array. , 2021, , .		3
8	In-situ learning in multilayer locally-connected memristive spiking neural network. Neurocomputing, 2021, 463, 251-264.	5.9	4
9	JUNO sensitivity to low energy atmospheric neutrino spectra. European Physical Journal C, 2021, 81, 1.	3.9	11
10	The design and sensitivity of JUNO's scintillator radiopurity pre-detector OSIRIS. European Physical Journal C, 2021, 81, 1.	3.9	15
11	Radioactivity control strategy for the JUNO detector. Journal of High Energy Physics, 2021, 2021, 1.	4.7	13
12	A rate-adjustable true random number generator based on the stochastic delay of a TiN/NbO _x /Pt memristor. AIP Advances, 2021, 11, .	1.3	3
13	A Symmetric Multilayer GeSe/GeSeSbTe Ovonic Threshold Switching Selector with Improved Endurance and Stability. , 2021, , .		1
14	Enhanced Spiking Neural Network with forgetting phenomenon based on electronic synaptic devices. Neurocomputing, 2020, 408, 21-30.	5.9	4
15	Configurable activation function realized by non-linear memristor for neural network. AIP Advances, 2020, 10, 085207.	1.3	3
16	A Self-Rectification and Quasi-Linear Analogue Memristor for Artificial Neural Networks. IEEE Electron Device Letters, 2019, 40, 1407-1410.	3.9	42
17	Voltage-control oscillator based on Pt/C/NbO _x /TiN device with highly improved threshold switching performances. Science China: Physics, Mechanics and Astronomy, 2019, 62, 1.	5.1	4
18	Transition from rectification to resistive-switching in Ti/MgF ₂ /Pt memory. AIP Advances, 2019, 9, 105117.	1.3	4

#	ARTICLE	IF	CITATIONS
19	Understanding the conduction and switching mechanism of Ti/AlO _x /TaO _x /Pt analog memristor. Physics Letters, Section A: General, Atomic and Solid State Physics, 2019, 383, 125877.	2.1	11
20	Quaternary synapses network for memristor-based spiking convolutional neural networks. IEICE Electronics Express, 2019, 16, 20190004-20190004.	0.8	9
21	A HfO ₂ /SiTe Based Dual-Layer Selector Device with Minor Threshold Voltage Variation. Nanomaterials, 2019, 9, 408.	4.1	23
22	A TaO _x -Based Electronic Synapse With High Precision for Neuromorphic Computing. IEEE Access, 2019, 7, 184700-184706.	4.2	6
23	Analysis, Design, and Order Estimation of Least-Squares FIR Equalizers for Bandwidth Extension of ADCs. Circuits, Systems, and Signal Processing, 2019, 38, 2165-2186.	2.0	1
24	Unidirectional threshold switching in Ag/Si-based electrochemical metallization cells for high-density bipolar RRAM applications. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	5
25	Short-Term and Long-Term Plasticity Mimicked in Low-Voltage Ag/GeSe/TiN Electronic Synapse. IEEE Electron Device Letters, 2018, 39, 492-495.	3.9	54
26	Threshold Switching Behavior of Ag-SiTe-Based Selector Device and Annealing Effect on its Characteristics. IEEE Journal of the Electron Devices Society, 2018, 6, 674-679.	2.1	26
27	A Ti/AlO _x /TaO _x /Pt Analog Synapse for Memristive Neural Network. IEEE Electron Device Letters, 2018, 39, 1298-1301.	3.9	41
28	Quasi-Analytical Model of 3-D Vertical-RRAM Array Architecture for MB-Level Design. IEEE Transactions on Electron Devices, 2017, 64, 1568-1574.	3.0	9
29	Impact of threshold voltage variation on 1S1R crossbar array with threshold switching selectors. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	2.3	20
30	A compliance current circuit with nanosecond response time for ReRAM characterization. , 2017, , .		1
31	Exploration of selector characteristic based on electron tunneling for RRAM array application. IEICE Electronics Express, 2017, 14, 20170739-20170739.	0.8	5
32	New write operation scheme for alleviating effect of line resistance on RRAM crossbar array. , 2016, , .		0
33	Analysis of the Negative-SET Behaviors in Cu/ZrO ₂ /Pt Devices. Nanoscale Research Letters, 2016, 11, 542.	5.7	18
34	Memory Devices: Eliminating Negative-SET Behavior by Suppressing Nanofilament Overgrowth in Cation-Based Memory (Adv. Mater. 48/2016). Advanced Materials, 2016, 28, 10809-10809.	21.0	6
35	An FPGA-based manipulation system for ReRAM characterization. , 2016, , .		0
36	Practical considerations of read-out circuits for passive, multi-level ReRAM arrays. , 2016, , .		2

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37	A memristor random circuit breaker model accounting for stimulus thermal accumulation. IEICE Electronics Express, 2016, 13, 20160376-20160376.	0.8	3
38	Impact of electroforming polarity on TiO_2 based memristor. IEICE Electronics Express, 2016, 13, 20160613-20160613.	0.8	1
39	Highly improved resistive switching performances of the self-doped Pt/HfO ₂ :Cu/Cu devices by atomic layer deposition. Science China: Physics, Mechanics and Astronomy, 2016, 59, 1.	5.1	13
40	Eliminating Negative SET Behavior by Suppressing Nanofilament Overgrowth in Cation-Based Memory. Advanced Materials, 2016, 28, 10623-10629.	21.0	189
41	Impact of active areas on electrical characteristics of TiO_2 based solid-state memristors. , 2015, , .		5
42	A Memristor SPICE Model Accounting for Synaptic Activity Dependence. PLoS ONE, 2015, 10, e0120506.	2.5	30
43	Coexistence of memory resistance and memory capacitance in TiO_2 solid-state devices. Nanoscale Research Letters, 2014, 9, 552.	5.7	29
44	High-Speed Real-Time Ion Detection System for Time-of-Flight Mass Spectrometry Application. Spectroscopy Letters, 2012, 45, 464-469.	1.0	2